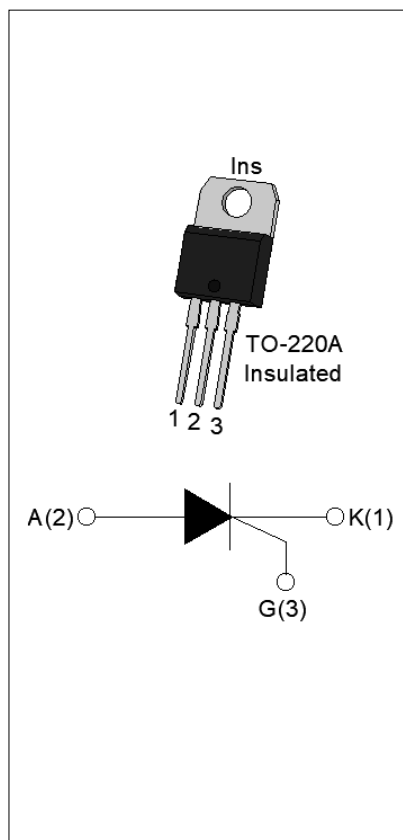




DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT151A-800R of silicon controlled rectifiers provides high dV/dt rate with strong resistance to electromagnetic interference. It is especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. From all three terminals to external heatsink, JCT151A-800R provides a rated insulation voltage of 2500 V_{RMS}, complying with UL standards (File ref: E252906).

Package TO-220A is RoHS compliant.



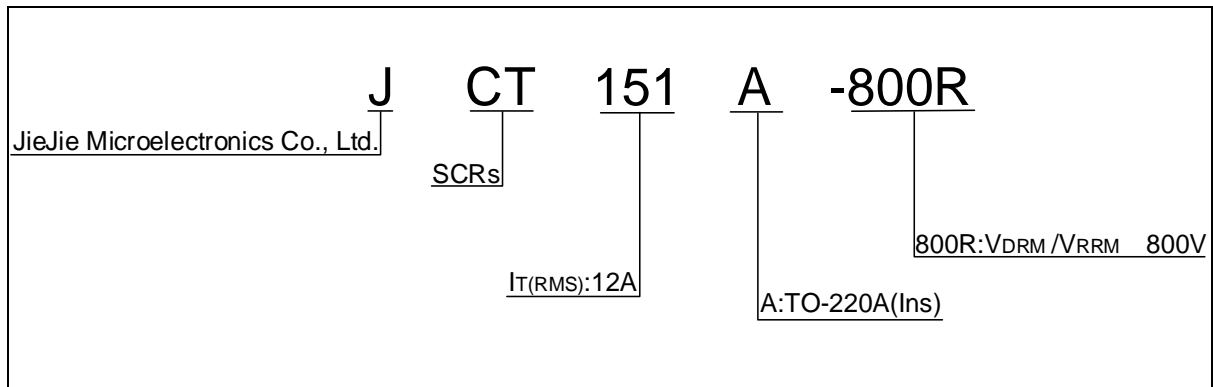
MAIN FEATURES

Symbol	Value	Unit
I _{T(RMS)}	12	A
V _{DRM} /V _{RPM}	800	V
I _{GT}	~15	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T _{stg}	-40-150	
Operating junction temperature range	T _j	-40-125	
Repetitive peak off-state voltage (T _j =25 °C)	V _{DRM}	800	V
Repetitive peak reverse voltage (T _j =25 °C)	V _{RPM}	800	V
Average on-state current (T _c 95 °C)	I _{T(AV)}	7.5	A
RMS on-state current (T _c 95 °C)	I _{T(RMS)}	12	A
Non repetitive surge peak on-state current (t _p =10ms, T _j =25 °C)	I _{TSM}	120	A
Non repetitive surge peak on-state current (t _p =8.3ms, T _j =25 °C)		132	
I ² t value for fusing (t _p =10ms, T _j =25 °C)	I ² t	72	A ² s
Critical rate of rise of on-state current (I _G =2x I _{GT} , f=100Hz, T _j =125 °C)	di/dt	100	A/s

ORDERING INFORMATION



MARKING

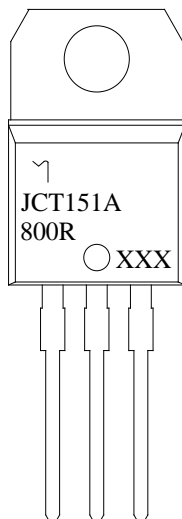
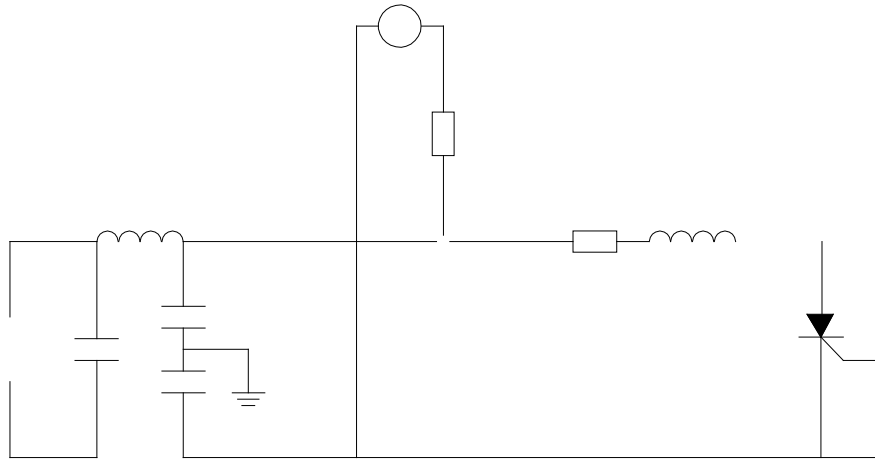


FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)		Package	
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Information furnished in this document is believed to be accurate and reliable.

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